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			APPLICANT Pierrat, et al.					
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	U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE		
PI)	4,231,811	11/4/80	Somekh, et al.	148	1.5	9/13/79		
- 	4,456,371	6/26/84	Lin	355	71	6/30/82		
	4,902,899	2/20/90	Lin, et al.	250	492.1	6/1/87		
	5,498,579	3/12/96	Borodovsky, et al.	437	250	6/8/94		
	5,553,274	9/3/96	Liebmann	395	. 500	6/6/95		
	5.636.002	6/3/97	Garofalo	.355	53	10/31/95		
.	5,663,017	9/2/97	Schinella, et al.	430	5	6/7/95		
-	5,723,233	3/3/98	Garza, et al.	430	5	2/27/96		
	5,766,806	6/16/98	Spence	430	5	9/9/96		
	5,821,014	10/13/98	Chen, et al.	430	5	2/28/97		
	5,862,058	1/19/99	Samuels, et al.	364	491	5/16/96		
	5,879,844	3/9/99	Yamamoto, et al.	430	30	12/20/96		
	5,885,734	3/23/99	Pierrat, et al.	430	. 5	8/15/96		
	5,900,338	5/4/99	Garza, et al.	430	5	8/15/97		
	5,994,002	11/30/99	Matsuoka	430	5	9/4/97		
	6,004,702	12/21/99	Lin	-430	5	5/21/98		
1	6,077,310	6/20/00	Yamamoto, et al.	716	19	1/29/99		
PD	6,078,738	6/20/00	Garza, et al.	395	500.22	5/8/97 .		
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			U.S. PATENT DOCU	MENTS	····	,,
EXAMINER'S INITIALS	PATENT NO:	DATE	NAME	CLASS	SUBCLASS	FILING DATE
FV	4,426,584	1/17/1984	Bohlen, et al.	250 -	492.2	6/3/198j
T/	4,895,780	1/23/1990	Nissan-Çohen, et al.	430	S	10/25/1988
	5,208,124	5/4/1993	Sporon-Fiedler, et al.	430	.\$	3/19/1991.
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
	5,972,541	10/26/1999	Sugasawara, ct al:	430	5	3/4/1998
	6,007,310	12/28/1999	Jacobsen; et al.	A1.7	- 362	5/23/1997
	6,114,071	9/5/2000	Chan, et al.	430	5.	4/6/1998
"	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
80	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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INFOR	MATION DIS CITATION PTO-1449		Atty. Docket No. NTI-019-5-1D Applicant PIERRAT, Chris Filing Date Filed Herewith	Fİİ	ed Herewith	
EXAMINER'S INITIALS	PATENT NO.	DATE	U.S. PATENT DOCUM	CLASS	SUBCLASS	FILING DATE
<u>PD</u>	6,014,456	1/11/2000	Tsudaka	382	144 .	7/15/1996
47	6,154,563	11/28/2000	Tsudaka ·	382	144	12/17/1998
	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
	6,453,457 B1	9/17/2002	. Pierrat, et al.	716	19	9/29/2000
PD	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	; š	3/15/2002

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00076	WO 00/67074.A1	11/9/2000	wo			YES	NO
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00077	WO 00/67075 A1	11/9/2000	WO				
00078	WO 00/67076 A-I	11/9/2000	wo	-			

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. (7)	3-80525	4/5/1991	JP ·					
11	2,324,169 A	10/14/1998	GB		-			
00	WO 99/47981	9/23/1999	wo					

EXAMINER: Date Considered:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPFP § 609; draw line through citation if first in conformance and not considered. Include copy of this form with next communication to applicant.

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INFOR	RMATION DISCLOSURE	NTI-019-5-1D Filed Herewith			
	CITATION	Applicant 10/679559			
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		Filed Herewith			
	OTHER DOCUMENTS	(Including Author, Title, Date, Pertinent Pages, Etc.)			
Ref ID	CITATION				
00082	Barouch, E., et al., "OPTIMASK: An OPC 192-206, February 1995.	C Algorithm for Chrome and Phase-Shift Mask Design*, SPIE, Vo. 2440, pp.			
00084	Brunner, T., et al., "Approximate Models	for Resist Processing Effects*, SPIE, Vol. 2726, pp. 198-207, March 1996.			
00085	Brunner, Tr., "Rim Phase-Shift Mask Com Geometries", Optical Engineering, Vol. 32	bined with Off-Axis Illumination: A Path to 0.5(lampda) / Numerical Aperture 2, No. 10, pp. 2337-2343, October 1993.			
00086	Casey, Jr., J.D., et al., "Chemically Enhanced FIB Repair of Opaque Defects on Molybdenum Silicide Photomasks", SPIE, Vol. 3236, pp. 487-497 (1997).				
00087	Chang, K., et al., "Accurate Modeling of I	Deep Submicron Interconnect Technology*, TMA Times, Vol. IX, No. 3 (1997).			
00094		echniques for DUV Photomasks", SPIE, Proceedings Of The 17th Annual and Management, Vol. 3236, pp. 136-141 (1997).			
00094	Symposium On Photomask Technology A				
	Symposium On Photomask Technology A Ham, Y.M., et al., "Dependence of Defect Henke, W., et al., "A Study of Reticle Def	and Management, Vol. 3236, pp. 136-141 (1997). s in Optical Lithography", Jpn. J. Appl. Phys., Vol. 31, pp. 4137-4142 (1992).			
00099	Symposium On Photomask Technology A Ham, Y.M., et al., "Dependence of Defect Henke, W., et al., "A Study of Reticle Def Using the Solid Lithography Simulator", h lbsen, K., et al., "Clear Field Reticle Defe	and Management, Vol. 3236, pp. 136-141 (1997). s in Optical Lithography*, Jpn. J. Appl. Phys., Vol. 31, pp. 4137-4142 (1992). Fects Imaged Into Three-Dimensional Developed Profiles of Positive Photoresist Microelectronics Eng., Vol. 14, pp. 283-297 (1991).			
00099	Symposium On Photomask Technology A Harn, Y.M., et al., "Dependence of Defect Henke, W., et al., "A Study of Reticle Def Using the Solid Lithography Simulator", N Ibsen, K., et al., "Clear Field Reticle Defe- The 17th Annual Symposium On Photoma Ishiwata, N., et al., "Novel Alternating Ph	and Management, Vol. 3236, pp. 136-141 (1997). s in Optical Lithography", Jpn. J. Appl. Phys., Vol. 31, pp. 4137-4142 (1992). fects Imaged Into Three-Dimensional Developed Profiles of Positive Photoresist Microelectronics Eng., Vol. 14, pp. 283-297 (1991). ct Diposition for Advanced Sub-Half Micron Lithography", SPIE, Proceedings Of			
00099 00101 00102	Symposium On Photomask Technology A Ham, Y.M., et al., "Dependence of Defect Henke, W., et al., "A Study of Reticle Defect Using the Solid Lithography Simulator", N lbsen, K., et al., "Clear Field Reticle Defect The 17th Annual Symposium On Photomas Ishiwata, N., et al., "Novel Alternating Ph. Annual Symposium On Photomask Techn	and Management, Vol. 3236, pp. 136-141 (1997). Is in Optical Lithography", Jpn. J. Appl. Phys., Vol. 31, pp. 4137-4142 (1992). Texts Imaged Into Three-Dimensional Developed Profiles of Positive Photoresist Microelectronics Eng., Vol. 14, pp. 283-297 (1991). It Diposition for Advanced Sub-Half Micron Lithography", SPIE, Proceedings Of ask Technology And Management, Vol. 3236, pp. 124-135 (1997). In Spiff Mask with Improved Phase Accuracy", SPIE, Proceedings Of The 17th ology And Management, Vol. 3236, pp. 243-249 (1997).			
00099 00101 00102 00105	Symposium On Photomask Technology A Harn, Y.M., et al., "Dependence of Defect Henke, W., et al., "A Study of Reticle Def Using the Solid Lithography Simulator", N Ibsen, K., et al., "Clear Field Reticle Defer The 17th Annual Symposium On Photoma Ishiwata, N., et al., "Novel Alternating Ph Annual Symposium On Photomask Techn Jinbo, H., et al., "0.2um or Less i-Line Litt	and Management, Vol. 3236, pp. 136-141 (1997). Is in Optical Lithography", Jpn. J. Appl. Phys., Vol. 31, pp. 4137-4142 (1992). Fects Imaged Into Three-Dimensional Developed Profiles of Positive Photoresist Microelectronics Eng., Vol. 14, pp. 283-297 (1991). In Diposition for Advanced Sub-Half Micron Lithography", SPIE, Proceedings Of ask Technology And Management, Vol. 3236, pp. 124-135 (1997). In See Shift Mask with Improved Phase Accuracy", SPIE, Proceedings Of The 17th Cology And Management, Vol. 3236, pp. 243-249 (1997). The Physics Shifting Mask Technology", IEEE, pp. 33.3.1-33.3.4 (1990). Thoughout those Shifting Lithography", IEEE, 1992 Symposium On VLSI Technology.			
00099 00101 00102 00105	Symposium On Photomask Technology A Ham, Y.M., et al., "Dependence of Defect Henke, W., et al., "A Study of Reticle Defect Using the Solid Lithography Simulator", h lbsen, K., et al., "Clear Field Reticle Defect The 17th Annual Symposium On Photomask Ishiwata, N., et al., "Novel Alternating Phi Annual Symposium On Photomask Techn Jinbo, H., et al., "0.2um or Less i-Line Litt Jinbo, H., et al., "Application of Blind Me Digest Of Technical Papers, pp. 112-113 (and Management, Vol. 3236, pp. 136-141 (1997). Is in Optical Lithography", Jpn. J. Appl. Phys., Vol. 31, pp. 4137-4142 (1992). Fects Imaged Into Three-Dimensional Developed Profiles of Positive Photoresist Microelectronics Eng., Vol. 14, pp. 283-297 (1991). In Diposition for Advanced Sub-Half Micron Lithography", SPIE, Proceedings Of ask Technology And Management, Vol. 3236, pp. 124-135 (1997). In See Shift Mask with Improved Phase Accuracy", SPIE, Proceedings Of The 17th Cology And Management, Vol. 3236, pp. 243-249 (1997). The Physics Shifting Mask Technology", IEEE, pp. 33.3.1-33.3.4 (1990). Thoughout those Shifting Lithography", IEEE, 1992 Symposium On VLSI Technology that the Phase-Shifting Lithography", IEEE, 1992 Symposium On VLSI Technology.			

		Atty. Docket No.	Scrial No.			
INFOR	MATION DISCLOSURE CITATION SUMMARY	NTI-019-5-10 Applicant PIERRAT, Christophe Füling Date	Filed Herewith 10/688559 Group 2825			
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" Ref ID	TCITATION TCITATION	(Including Author, Title, Date	e, Pertinent Pages, Etc.)			
00110						
00115	Lithas, "Lithas: Optical Proximity Correc	ation Software* (2 pages). Date	not available)			
00118	Microunity, "OPC Technology & Product	Description", MicroUnity Systems Engine	eering, Inc., pp. 1-5.			
00120	Morimoto, H., et al., "Next Generation M Vol. 3236, pp. 188-189 (1997).	ask Strategy • Technologies are Ready for	Mass Production of 256MDRAM?", SPIE,			
00121	Nistler, J., et al., "Large Area Optical Des Technology, Vol. 2254, pp. 78-92 (1994).		ion", SPIE, Photomask And X-Ray Mask			
00122	Nistler, J., et al., "Phase Shift Mask Defect INTERFACE '93, OCG Microelectronic I		he Microlithography Seminar			
00123	Ohtsuka, H., et al., "Phase Defect Repair Appl. Phys., Vol. 31, pp. 4143-4149 (199)		Conjugate Twin-Shifter Method*, Jpn. J.			
00124	Park, C., et al., "An Automatic Gaie CD C	Control for a Full Chip Scale SRAM Device	e", SPIE, Vol. 3236, pp. 350-357 (1997).			
00125	Pati, Y.C., et al., "Exploiting Structure in On Semiconductor Manufacturing, Vol. I		med Circuit Patterns*, IEEE Transactions			
00126	Pati, Y.C., et al., "Phase-Shifting Masks for Microlithography: Automated Design and Mask Requirements", J. Opt. Soc. Am., Vol. 11, No. 9, pp. 2438-2452, September 1994.					
00128	Precim, "Proxima System", Precim Company, Portland, Oregon (2 pages). (Date not available)					
00129	Precim, "Proxima Wafer Proximity Correction System", Precim Company, Portland, Oregon (2 pages). (Date not available)					
. 00130	Rieger, M., et al., "Customizing Proximity		es", SPIE, Vol. 2726, pp. 651-659 (1996).			
00131	Rieger, M., et al., "Mask Fabrication Rule	s for Proximity-Corrected Patterns", Preci	m Company, Portland, Oregon (10 pages).			

		Atty. Docket No. Serial No.		
INFOR	MATION DISCLOSURE	NTI-019-5-1D Filed Herewith		
CITATION		Applicant 10/638559		
		, , , , , ,		
	SUMMARY	PIERRAT, Christophe Filing Date 10 16 03 Group 2825		
		Filed Herewith		
	OTHER DOCUMENTS	(Including Author, Title, Date, Pertinent Pages, Etc.)		
Ref ID	CITATION			
00132	Rieger, M., et al., "System for Lithograph (28 pages).	y Proximity Compensation*, Precim Company, Portland, Oregon, September 1993		
00133	Rieger, M., et al., "Using Behavior Model	ing for Proximity Correction", Presim Company, Portland, Oregon (6 pages). Le Not awayable)		
00134	Roman, B., et al., "Implications of Device Only).	Processing on Photomask CD Requirements*, SPIE, Vol. 3236 (1997) (Abstract		
00136	Spence, C., et al., "Automated Determination of CAD Layout Failures Through Focus: Experiment and Simulation", SPIE, Vol. 2197, pp. 302-313 (1994).			
00137	Spence, C., et al., "Detection of 60(degree DuPont RTC (2 pages).	e) Phase Defects on Alternating PSMs", Advanced Micro Devices, KLA-Tencor, e not awai abe		
00140	Stimiman, J., et al., 'Fast Proximity Corre	ection with Zone Sampling", SPIE, Vol. 2197, pp. 294-301 (1994).		
00141	Stimiman, J., et al., "Optimizing Proximit Management, Vol. 2322, pp. 239-246 (19	y Correction for Wafer Fabrication Processes", SPIE, Photomask Technology And 94).		
00142		s to Describe IC Lithographic Behavior", Precim Corporation, Portland, Oregon (10 ot available)		
00143	Stimiman, J., et al., "Wafer Proximity Co. 10-12, January 1994.	rrection and its Impact on Mask-Making", Bacus News, Vol. 10, Issue 1, pp. 1, 3-7,		
00144 .	Sugawara, M., et al., "Defect Printability Study of Attenuated Phase-Shifting Masks for Specifying Inspection Sensitivity", Sony Corporation, Kanagawa, Japan (16 pages). (Date not awar Lable)			
00146	Trans Vector, "Now Better Quality Photomasks", Trans Vector Technologies, Inc., Camarillo, California (4 pages). (Date not available)			
00147	Vacca, A., et al., "100nm Defect Detection Using a Dynamically Programmable Image Processing Algorithm", SPIE, Vol. 3236 (1997) (Abstract Only).			
00148	Vacca, A., et al., "100nm Defect Detection	n Using an Existing Image Acquisition System", SPIE, Vol. 3236, pp. 208-21 (1998		
00149	Watanabe, H., et al., "Detection and Print Appl. Phys., Vol. 31, pp. 4155-4160 (199	ability of Shifter Defects in Phase-Shifting Masks [I Defocus Characteristics*; Jpn. J 2).		

	INFOR	MATION DISCLOSURE CITATION SUMMARY	Atty. Docket No. NTI-019-5-1D Filed Herewith Applicant PIERRAT, Christophe Filing Date 0 6 6 7 7 Filed Herewith			
		OTHER DOCUMENTS	(Including Author, Title, Date, Pertinent Pages, Etc.)			
	Ref ID ·	CITATION				
) [00150	Wiley, J., et al., "Device Yield and Reliab 65-66, 70, 72, 74, 77, July 1993.	ility by Specification of Mask Defects", Solid State Technology, Vol. 36, No. 7, pp.			
Ť	00151	Wiley, J., et al., "The Effect of Off-Axis I Vol. 2512, pp. 432-440 (1995).	humination on the Printability of Opaque and Transparent Reticle Defects", SPIE,			
· [00152	Wiley, J., et al., "Phase Shift Mask Pattern Accuracy Requirements and Inspection Technology", SPIE, Integrated Circuit Metrology, Inspection, And Process Control V, Vol. 1464, pp. 346-355 (1991).				
T	00153	Yen, A., et al., "Characterization and Correction of Optical Proximity Effects in Deep-Ultraviolet Lithography Using Behavior Modeling", J. Vac. Sci. Technol. B, Vol. 14, No. 6, pp. 4175-4178, November/December 1996.				
T	00157	Cobb, et al., "Fast Sparse Aerial Image Calculation for OPC", SPIE, Vol. 2621, pp. 534-544, September 20-22, 1995.				

INFORMATION DISCLOSURE CITATION PTO-1449 APPLICANT Pierrat, et al. APPLICANT Pierrat, et al. APPLICANT Pierrat, et al. Fled Herewith OTHER DOCUMENTS (Including Author, Title, Date, Perfinent Pages, Etc.) Ackmann, P. et al., "Phase Shifting And Optical Proximity Corrections To Improve CD Control On Logic Devices In Manufacturing For Sub 0.35 µm l-Line", Advance Micro Devices (8 pages). Asia, N. et al., "Proposal For The Come Aberration Dependent Overlay Error Compensation Technology", Jan. J. Appl. Phys., Vol. 37, pp. 6718-6722 (1998). Chen, J.F. et al., "Full-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlindography World (1997). Chen, J.F. et al., "Poll-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlindography World (1997). Chen, J.F., et al., "Full-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlinity Systems Engineering, Inc., Sunnyvale, California, pp. 1-16. (And The Depth of Proximity Correction For Intermediate-Pitch Features Using Sub-Resolution Seattering Bars", Microlinity Systems Engineering, Inc., Sunnyvale, California (14 pages). Chen, J.F., et al., "Practical Method For Full-Lipi Optical Proximity Correction", Microlinity Systems Engineering, Inc., Sunnyvale, California (14 pages). Garofalo, J. et al., "Automatic Layout Of Mask Assist-Features For Realizing 0.5k; ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 µm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotob, Y. et al., "Pattern Dependent Aligament Technique For Micro. And Match Electron-Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 12, No. 10, pp. 1508-1514, October 1993. Preci				1/22		
APPLICANT Pierrat, et al., FILING DATE Fled Herewith GROUP 232 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Ackmann, P. et al., "Phase Shifting And Optical Proximity Corrections To Improve CD Control On Logic Devices In Manufacturing For Sub 0.35 µm I-Line", Advance Micro Devices (8 pages). Date No. 1. (Max. 2 hape.) Asia, N. et al., "Proposal For The Coma Aberration Dependent Overlay Error Compensation Technology", Jpn. J. Appl. Phys., Vol. 37, pp. 6718-6722 (1998). Chen, J.F. et al., "Full-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlithography World (1997). Chen, J.F. et al., "Optical Proximity Correction For latermediate-Pitch Features Using Sub-Resolution Scattering Bars", Microlinity Systems Engineering, Inc., Sunnyvale, California, pp. 1-16. Chen, J.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", Microlinity Systems Engineering, Inc., Sunnyvale, California (14 pages). Carofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k; ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k; ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 µm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Priat Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierra, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).	== : - :			SERIAL NO. 1 9 68 3 55 9 Filed Herewith		
TELING DATE Fled Herwith GROUP 232 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Ackmann, P. et al., "Phase Shifting And Optical Proximity Corrections To Improve CD Control On Logic Devices In Manufacturing For Sub 0.35 µm I-Line", Advance Micro Devices (8 pages). Devices In Manufacturing For Sub 0.35 µm I-Line", Advance Micro Devices (8 pages). Devices In Manufacturing For Sub 0.35 µm I-Line", Advance Micro Devices (8 pages). Devices In Manufacturing For Sub 0.35 µm I-Line", Advance Micro Devices (8 pages). Devices In Manufacturing For Sub 0.35 µm I-Line Photolithography World (1997). Chen, J.F., et al., "Full-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlithography World (1997). Chen, J.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Chen, J.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k, ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k, ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 µm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix-And-Match Electron-Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fab			APPLICANT Pierrat, et al,			
Ackmann, P. et al., "Phase Shifting And Optical Proximity Corrections To Improve CD Control On Logic Devices In Manufacturing For Sub 0.35 µm I-Ling", Advance Micro Devices (8 pages). Asai, N. et al., "Proposal For The Coma Aberration Dependent Overlay Error Compensation Technology", Jpn. J. Appl. Phys., Vol. 37, pp. 6718-6722 (1998). Chen, J.F. et al., "Full-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlithography World (1997). Chen, J.F. et al., "Optical Proximity Correction For Intermediate-Pitch Features Using Sub-Resolution Scattering Bars", Microlinity Systems Engineering, Inc., Sunnyvale, California, pp. 1-16. Chen, J.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", Microlinity Systems Engineering, Inc., Sunnyvale, California (14 pages). Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k; ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 µm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Aligament Technique For Mix-And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", J. Ete., Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).		:	FILING DATE Filed Herewith	GROUP 2325		
Devices In Manufacturing For Sub 0.35 µm I-Line", Advance Micro Devices (8 pages). Asia, N. et al., "Proposal For The Coma Aberration Dependent Overlay Error Compensation Technology", Jpn. J. Appl. Phys., Vol. 37, pp. 6718-6722 (1998). Chen, J.F. et al., "Full-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlithography World (1997). Chen, J.F. et al., "Optical Proximity Correction For Intermediate-Pitch Features Using Sub-Resolution Scattering Bars", MicroUnity Systems Engineering, Inc., Sunnyvale, California, pp. 1-16. (Att Not auxiliable) Chen, J.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k; ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 µm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix-And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", J.EEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lia, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).		OTHER DOCUMENTS	Including Author, Title, Date, Pertin	ent Pages, Etc.)		
Jpn. J. Appl. Phys., Vol. 37, ipp. 6718-6722 (1998). Chen., I.F. et al., "Full-Chip Optical Proximity Correction With Depth Of Focus Enhancement", Microlithography World (1997). Chen., I.F. et al., "Optical Proximity Correction For Intermediate-Pitch Features Using Sub-Resolution Scattering Bars", MicroUnity Systems Engineering, Inc., Surnivvale, California, pp. 1-16. Chen., I.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Date Not available) Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k; ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 µm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix. And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierra, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).	PD	Ackmann, P. et al., "Phase Sh Devices In Manufacturing For	Sub 0.35 µm I-Line", Advance Micro Devices (8 pages).			
Microlithography World (1997). Chen, J.F. et al., "Optical Proximity Correction For Intermediate-Pitch Features Using Sub-Resolution Scattering Bars", MicroUnity Systems Engineering, Inc., Sunnyvale, California, pp. 1-16. Chen, J.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Carolina Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Carolina Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Carolina Carolina Carolina Carolina Carolina California (14 pages). Carolina	· \			lay Error Compensation Technology",		
Scattering Bars", MicroUnity Systems Engineering, Inc., Sumyvale, California, pp. 1-16. Chen, J.F., et al., "Practical Method For Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages). Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k1 ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 µm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix-And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", JEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k1 Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).				h Of Focus Enhancement",		
Engineering, inc., Sunnyvale, California (14 pages). Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k ₁ ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 μm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix-And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).		Chen, J.F. et al., "Optical Pro- Scattering Bars", MicroUnity	Systems Engineering, Inc., Sunnyvale,	California, pp. 1-16.		
SPIE, Vol. 2440, pp. 302-312 (1995). Garofalo, J. et al., "Automatic Proximity Correction For 0.35 μm I-Line Photolithography", IEEE, pp. 92-94 (1994). Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix-And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).			0 1:0 1:00			
Garofalo, J. et al., "Mask Assisted Off-Axis Illumination Technique For Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix-And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).		Garofalo, J. et al., "Automated Layout Of Mask Assist-Features For Realizing 0.5k, ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995).				
Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993. Gotoh, Y. et al., "Pattern Dependent Alignment Technique For Mix-And-Match Electron-Beam Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).			: Proximity Correction For 0.35 µm I-L	ine Photolithography", IEEE, pp. 92-94		
Lithography With Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998. Harafuji, K. et al., "A Novel Hierarchical Approach For Proximity Effect Correction In Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).		Garofalo, J. et al., "Mask Ass Technol. B, Vol. 11, No. 6, pp	isted Off-Axis Illumination Technique b. 2651-2658, November/December 199	For Random Logic", J. Vac. Sci.		
Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993. Lin, B.J., "Methods To Print Optical Images At Low-k, Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).		Lithography With Optical Lit				
Vol. 1264, pp. 2-13 (1990). Pierrat, C. et al., "A Rule-Based Approach To E-Beam And Process-Induced Proximity Effect Correction For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).						
For Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).						
Precim, "Proxima System", Precim Company, Portland, Oregon (2 pages). (Date not available) EXAMINER PAUL DATE CONSIDERED 2 2186						
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INFORMATION DISCLOSURE CITATION PTO-1449		ATTY. DOCKET NO.	SERIAL NO. 10/688559 Filed Herewith	
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PP	Saleh, B. et al., "Reduction Of Errors Of Microphotographic Reproductions By Optimal Corrections Of Original Masks", Optical Engineering, Vo. 20, No. 5, pp. 781-784, September/October 1981.			
PD	Spence, C. et al., "Integration Of Optical Proximity Correction Strategies In Strong Phase Shifters Design For Poly-Gate Layers", Bacus News, Vol. 15, Issue 12, pp. 1, 4-13, December 1999.			
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SHEET 14 of 17 Atty. Docket No. Serial No. INFORMATION DISCLOSURE NTI-019-5-1D Filed Herewith CITATION Applicant PIERRAT, Christophe PTO-1449 Group Filing Date Filed Herewith OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) EXAMINER'S CITATION INITIALS Choi, Y., et al., "Optical Proximity Correction on Attenuated Phase Shifting Photo Mask for Dense Contact Army", LG Semicon Company (11 pages). Date Not avai lable Lucas, K., et al., "Model Based OPC for 1st Generation 193nm Lithography", Motorola Inc., IDT assignee to IMEC (12 pages). Date not available Stirriman, J., et al., "Quantifying Proximity and Related Effects in Advanced Wafer Processes", Precim Company, Hewlett Packard Labs (9 pages). Date not available Sugawara, M., et al., "Practical Evaluation of Optical Proximity Effect Correction by EDM Methodology", Sony Corporation (11 Jen avai lable Granik, Y., et al., "MEEF as a Matrix", Mentor Graphics Corporation (11 pages). not avai able Kang, D., et al., "Effects of Mask Bias on the Mask Error Enhancement Factor (MEEF) of Contact Holes" (11 pages). available Not Matsuura, S., et al., "Reduction of Mask Error Enhancement Factor (MEEF) by the Optimum Exposure Dose Self-Adjusted Mask", NEC Corporation (12 pages). available Saleh, B., et al., "Reduction of Errors of Microphotographic Reproductions by Optimal Corrections of Original Masks", Optical Engineering, Vol. 20, No. 5, pp. 781-784, September/October 1981. Fu, C.C., et al., "Enhancement of Lithographic Patterns by Using Serif Features", IEEE, Transactions On Electron Devices, Vol. 38, No. 12, pp. 2599-2603, December 1991. Henderson, R., et al., "Optical Proximity Effect Correction: An Emerging Technology", Microlithography World, pp. 6-12 Dolainsky, C., et al., "Application of a Simple Resist Model to Fast Optical Proximity Correction", SPIE, Vol. 3051, pp. 774-780 Chen, J., et al., "Full-Chip Optical Proximity Correction with Depth of Focus Enchancement", Microlithography World ,(5 pages) (1997). Wong, A., et al., "Lithographic Effects of Mask Critical Dimension Error", SPIE, Vol. 3334, pp. 106-115 (1998). Spence, C., et al., "Integration of Optical Proximity Correction Strategies in Strong Phase Shifters Design for Poly-Gate Layers", Bacus News, Vol. 15, Issue 12, pp. 1, 4-13, December 1999.

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Atty. Docket No. Serial No. INFORMATION DISCLOSURE NTI-019-5-1D Filed Herewith **CITATION Applicant** PIERRAT, Christophe PTO-1449 Group Filing Date Filed Herewith OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) CITATION **EXAMINER'S** INITIALS Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).

EXAMINER: Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered, include copy of this form with next communication to applicant.

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OTHER DOCUMENTS	(Including Author, Title, Date	, Pertinent Pages, Etc.)
EXAMINER'S CITATION INITIALS		•
Chiuang, H., et al., "Practical Applications Logic Devices", IEEE, pp. 18.7.1-18.7.4,	of 2-D Optical Proximity Corrections for E December 1997.	nhanced Performance of 0.25um Random

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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformatice and not considered. Include copy of this form with next communication to applicant.

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•	OTHER DOCUMENTS	(Including Author, Title, D	ate, Pertinent Pages, Etc.)		
EXAMINER'S INITIALS	CITATION				
P D	Cobb, N., et al., 'Fast, Low-Complexity Mask Design', SPIE, Vol. 2440, pp. 313-327, February 22-24; 1995.				
	Cobb, N., et al., "Experimental Results on Optical Proximity Correction With Variable Threshold Resist Model", SPIE, Vol. 3051, pp. 458-468, March 12-14, 1997.				
	Cobb, N., "Fast Optical and Process Proximity Correction Algorithms for Integrated Circuit Manufacturing", Dissertation, University of California at Berkeley, UMI Microform 9907038 (139 pages). (Date not available)				
99	Toublan, O., et al., "Phase Aware Proximi	ty Correction for Advanced Masks*, SP	IE, Vol. 4000, pp. 160-170, March 1-3, 2000.		

EXAMINER: Jaul Date Considered:

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EXAMINER: Initial if reference considered. Whether or not citation is in conformance with MPFP 6 609: draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.